



NPN LOW POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/368

DESCRIPTION

This family of high-frequency, epitaxial planar transistors feature low saturation voltage. These devices are also available in TO-39 and low profile U4 and UA packaging. Microsemi also offers numerous other transistor products to meet higher and lower power ratings with various switching speed requirements in both through-hole and surface-mount packages.

Important: For the latest information, visit our website http://www.microsemi.com.

FEATURES

- JEDEC registered 2N3439 through 2N3440 series.
- JAN, JANTX, JANTXV, and JANS qualifications are available per MIL-PRF-19500/368.
- RoHS compliant versions available (commercial grade only).
- $V_{CE(sat)} = 0.5 V @ I_C = 50 mA.$
- Turn-On time t_{on} = 1.0 μs max @ I_{C} = 20 mA, I_{B1} = 2.0 mA.
- Turn-Off time $t_{off} = 10 \ \mu s \ max @ I_C = 20 \ mA$, $I_{B1} = -I_{B2} = 2.0 \ mA$.

APPLICATIONS / BENEFITS

- General purpose transistors for medium power applications requiring high frequency switching and low package profile.
- Military and other high-reliability applications.

MAXIMUM RATINGS (T_c = +25°C unless otherwise noted)

Parameters / Test Conditions		Symbol	2N3439	2N3440	Unit
Collector-Emitter Voltage		V _{CEO}	350	250	V
Collector-Base Voltage	Collector-Base Voltage		450	300	V
Emitter-Base Voltage		V _{EBO}	7.0		V
Collector Current		Ι _C	1.0		Α
Total Power Dissipation	@ $T_A = +25^{\circ}C^{(1)}$ @ $T_C = +25^{\circ}C^{(2)}$	PD	0.8 5.0		W
Operating & Storage Junction Temperature Range		T_J, T_stg	-65 to +200		°C

<u>Notes</u>: 1. Derate linearly @ 4.57 mW/°C for T_A > +25°C.

2. Derate linearly @ 28.5mW/°C for T_C > +25°C

<u>Qualified Levels</u>: JAN, JANTX, JANTXV and JANS



TO-39 (TO-205AD) Package

Also available in:

TO-5 package (long leaded) 2N3439L - 2N3440L

U4 package (surface mount) 2N3439U4 – 2N3440U4

UA package (surface mount) 2N3439UA - 2N3440UA

MSC – Lawrence

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MSC – Ireland

Gort Road Business Park, Ennis, Co. Clare, Ireland Tel: +353 (0) 65 6840044 Fax: +353 (0) 65 6822298

Website:

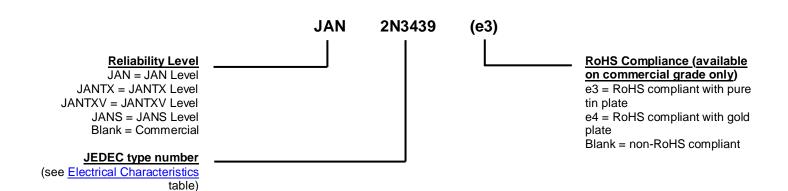
www.microsemi.com



MECHANICAL and PACKAGING

- CASE: Hermetically sealed, kovar base, nickel cap.
- TERMINALS: Tin/lead solder dip or RoHS compliant pure tin (commercial grade only) plate over gold.
- MARKING: Part number, date code, manufacturer's ID.
- POLARITY: NPN (see package outline).
- WEIGHT: Approximately 1.064 grams.
- See <u>Package Dimensions</u> on last page.

PART NOMENCLATURE



	SYMBOLS & DEFINITIONS				
Symbol	Definition				
C _{obo}	Common-base open-circuit output capacitance.				
I _{CEO}	Collector cutoff current, base open.				
I _{CEX}	Collector cutoff current, circuit between base and emitter.				
I _{EBO}	Emitter cutoff current, collector open.				
h _{FE}	Common-emitter static forward current transfer ratio.				
V _{CEO}	Collector-emitter voltage, base open.				
V _{CBO}	Collector-emitter voltage, emitter open.				
V _{EBO}	Emitter-base voltage, collector open.				



ELECTRICAL CHARACTERISTICS ($T_A = +25^{\circ}C$, unless otherwise noted)

OFF CHARACTERISTICS

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
Collector-Emitter Breakdown Voltage $I_C = 10 \text{ mA}$ $R_{BB1} = 470 \Omega; V_{BB1} = 6 V$ L = 25 mH (min); f = 30 - 60 Hz	2N3439 2N3440	V _{(BR)CEO}	350 250		V
Collector-Emitter Cutoff Current $V_{CE} = 300 V$ $V_{CE} = 200 V$	2N3439 2N3440	I _{CEO}		2.0 2.0	μA
Emitter-Base Cutoff Current $V_{EB} = 7.0 V$		I _{EBO}		10	μA
Collector-Emitter Cutoff Current $V_{CE} = 450 \text{ V}, V_{BE} = -1.5 \text{ V}$ $V_{CE} = 300 \text{ V}, V_{BE} = -1.5 \text{ V}$	2N3439 2N3440	I _{CEX}		5.0 5.0	μA
Collector-Base Cutoff Current $V_{CB} = 360 V$ $V_{CB} = 250 V$ $V_{CB} = 450 V$ $V_{CB} = 300 V$	2N3439 2N3440 2N3439 2N3440	I _{CBO}		2.0 2.0 5.0 5.0	μA

ON CHARACTERISTICS (1)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Forward-Current Transfer Ratio $I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 2.0 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 0.2 \text{ mA}, V_{CE} = 10 \text{ V}$	h _{FE}	40 30 10	160	
Collector-Emitter Saturation Voltage $I_{C} = 50 \text{ mA}, I_{B} = 4.0 \text{ mA}$	V _{CE(sat)}		0.5	V
Base-Emitter Saturation Voltage $I_{C} = 50 \text{ mA}, I_{B} = 4.0 \text{ mA}$	V _{BE(sat)}		1.3	V

DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Magnitude of Common Emitter Small-Signal Short- Circuit Forward Current Transfer Ratio $I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}, f = 5.0 \text{ MHz}$	h _{fe}	3.0	15	
Forward Current Transfer Ratio $I_{C} = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}, f = 1.0 \text{ kHz}$	h _{fe}	25		
Output Capacitance V _{CB} = 10 V, I _E = 0, 100 kHz \leq f \leq 1.0 MHz	C _{obo}		10	pF
Input Capacitance $V_{CB} = 5.0 \text{ V}, I_E = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz}$	C _{ibo}		75	pF

(1) Pulse Test: Pulse Width = 300 μ s, duty cycle \leq 2.0%.



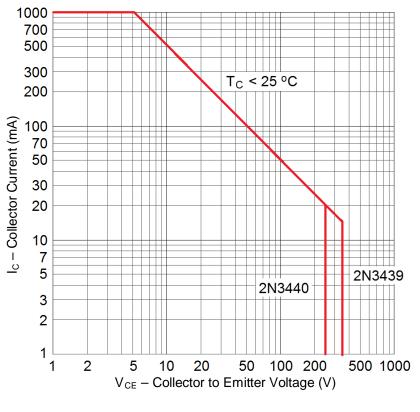
ELECTRICAL CHARACTERISTICS ($T_A = +25^{\circ}C$, unless otherwise noted) continued

SWITCHING CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Turn-On Time V_{CC} = 200 V; I _C = 20 mA, I _{B1} = 2.0 mA	t _{on}		1.0	μs
Turn-Off Time V _{CC} = 200 V; I _C = 20 mA, I _{B1} = -I _{B2} = 2.0 mA	t _{off}		10	μs

SAFE OPERATING AREA (See graph below and also reference test method 3053 of

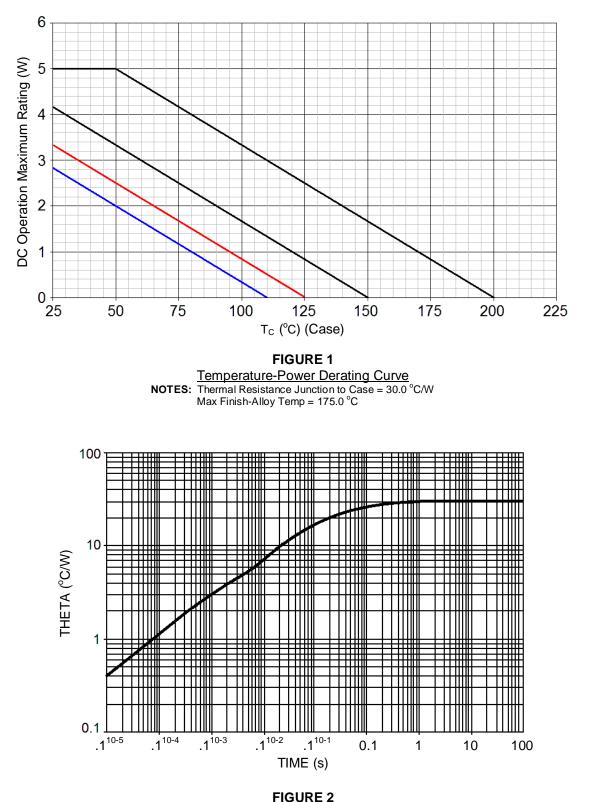
<u>MIL-STD-750</u> .)	
DC Tests	
T _C = +25 °C, 1 Cycle, t = 1.0 s	
Test 1	
$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ A}$	Both Types
Test 2	
V _{CE} = 350 V, I _C = 14 mA	2N3439
Test 3	
$V_{CE} = 250 \text{ V}, I_{C} = 20 \text{ mA}$	2N3440



Maximum Safe Operating graph (continuous dc)



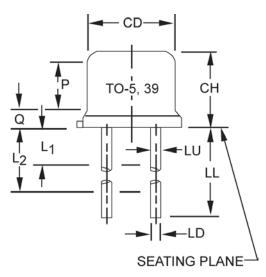
GRAPHS



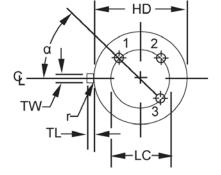
Maximum Thermal Impedance NOTE: $T_c = +25 \text{ °C}, P_T = 5.0 \text{ W}$, thermal resistance $R_{\text{BUC}} = 30 \text{ °C/W}$, steel.



PACKAGE DIMENSIONS



	Dimensions					
Symbol	Incl	nes	Millimeters		Note	
	Min	Max	Min	Max		
CD	.305	.335	7.75	8.51	6	
СН	.240	.260	6.10	6.60		
HD	.335	.370	8.51	9.40		
LC	.200) TP	5.08 TP		7	
LD	.016	.019	0.41	0.48	8,9	
LL						
LU	.016	.019	0.41	0.48	8,9	
L1		.050		1.27	8,9	
L2	.250		6.35		8,9	
Р	.100		2.54		7	
Q		.030		0.76	5	
TL	.029	.045	0.74	1.14	3,4	
TW	.028	.034	0.71	0.86	3	
r		.010		0.25	10	
α	45° TP		45° TP		7	



NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. Beyond r (radius) maximum, TW shall be held for a minimum length of .011 (0.28 mm).
- 4. Dimension TL measured from maximum HD.
- 5. Body contour optional within zone defined by HD, CD, and Q.
- 6. CD shall not vary more than .010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
- 7. Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods or by gauging procedure.
- 8. Dimension LU applies between L1 and L2. Dimension LD applies between L2 and LL minimum. Diameter is uncontrolled in and beyond LL minimum.
- 9. All three leads.
- 10. The collector shall be internally connected to the case.
- 11. Dimension r (radius) applies to both inside corners of tab.
- 12. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.
- 13. Lead 1 =emitter, lead 2 =base, lead 3 =collector.
- 14. For transistor types 2N3439 and 2N3440 (TO-39), dimension LL = .5 inch (12.70 mm) min. and .750 inch (19.05 mm) max.